ABSTRACT

Defect analysis of an integrated circuit die having a back side opposite circuitry at a circuit side and a liquid crystal layer is enhanced using near infrared (nIR) laser light. According to an example embodiment of the present invention, nIR laser light is directed to an integrated circuit die having a liquid crystal layer formed over the die. When the die includes a defect that generates heat, the heat generated in the die as a result of the nIR laser light adds to the heat in the die generated as a result of the defect and causes a portion of the liquid crystal layer to change phase near the defect. The phase change is detected and used to identify a portion of the die having a defect.